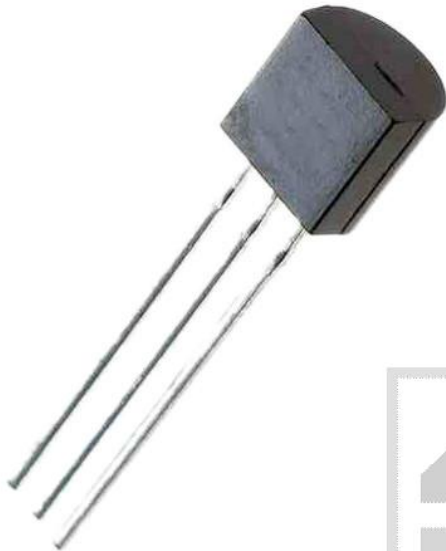




TR BC327-25;LGE;TO92;tranzystor; PNP;0.8A;50V;0.625W;Pbf



Dane techniczne:

Nazwa: BC327-25

Typ tranzystora: bipolarny

Kierunek przewodnictwa: PNP

Prąd kolektora: 0.8A

Napięcie kolektor-emiter: 50V

Moc: 0.625W

Obudowa: TO92

Montaż: przewlekany (THT)

Producent: LGE



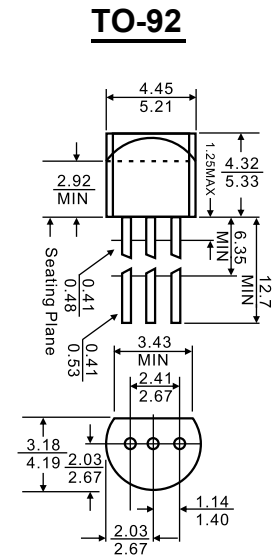
1. COLLECTOR
2. BASE
3. EMITTER

Features

- ◇ Power dissipation

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage BC327	-50	V
	BC328	-30	
V _{CEO}	Collector-Emitter Voltage BC327	-45	V
	BC328	-25	
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-800	mA
P _C	Collector Power Dissipation	625	mW
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



Dimensions in inches and (millimeters)

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{CB0}	I _C = -100uA, I _E =0	-50			V
			-30			
Collector-emitter breakdown voltage	V _{CEO}	I _C = -10mA, I _B =0	-45			V
			-25			
Emitter-base breakdown voltage	V _{EBO}	I _E = -10uA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -45 V, I _E =0 V _{CB} = -25V, I _E =0			-0.1	uA
					-0.1	
Collector cut-off current	I _{CEO}	V _{CE} = -40 V, I _B =0 V _{CE} = -20 V, I _B =0			-0.2	uA
					-0.2	
Emitter cut-off current	I _{EBO}	V _{EB} = -4 V, I _C =0			-0.1	uA
DC current gain	h _{FE(1)}	V _{CE} =-1 V, I _C = -100mA	100		630	
	h _{FE(2)}	V _{CE} =-1 V, I _C = -300mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500mA, I _B = -50mA			-0.7	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -500mA, I _B =-50mA			-1.2	V
Base-emitter voltage	V _{BE}	V _{CE} =-1 V, I _C = -300mA			-1.2	V
Transition frequency	f _T	V _{CE} = -5V, I _C = -10mA f = 100MHz	260			MHz
Collector Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0 f=1MHz		12		pF

CLASSIFICATION OF h_{FE}

Rank	16	25	40
Range	100-250	160-400	250-630

BC327/328(PNP)

TO-92 Bipolar Transistors

Typical Characteristics

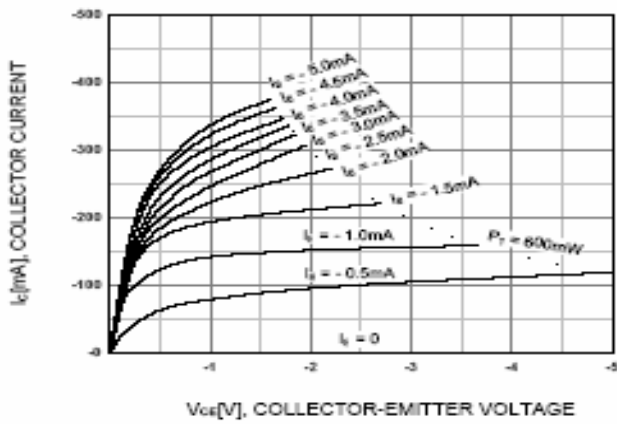


Figure 1. Static Characteristic

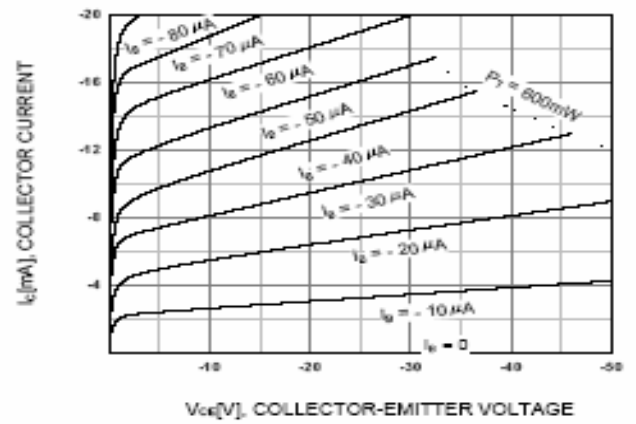


Figure 2. Static Characteristic

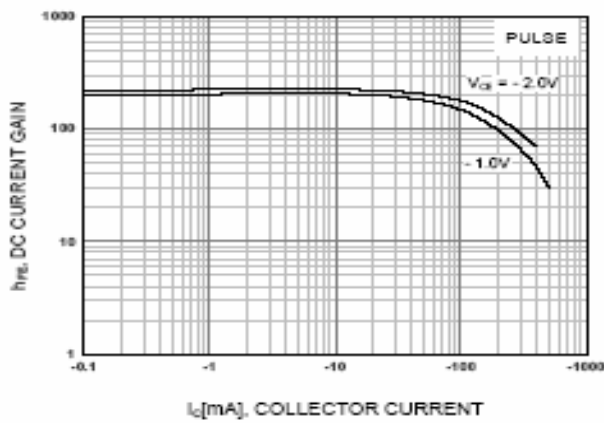


Figure 3. DC current Gain

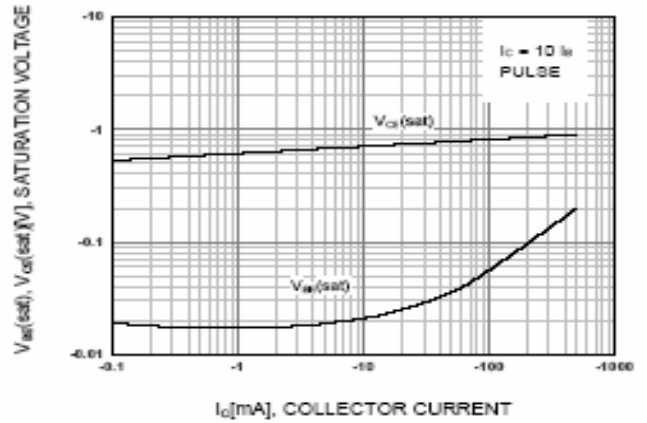


Figure 4. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

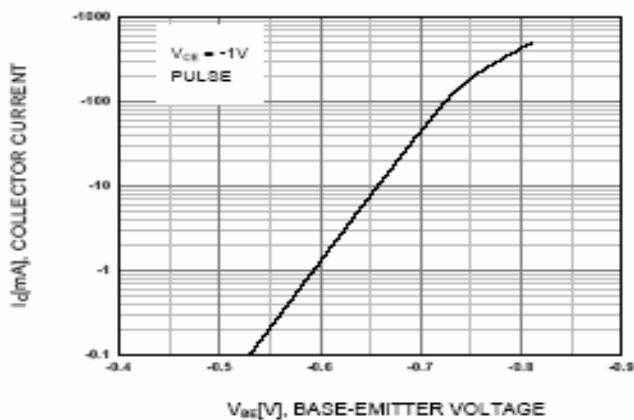


Figure 5. Base-Emitter On Voltage

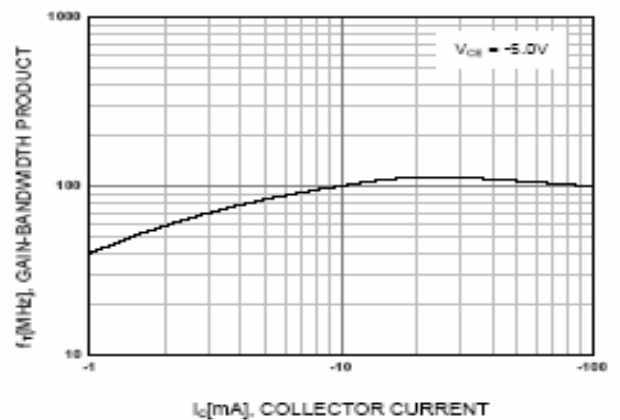


Figure 6. Gain Bandwidth Product

BC327/328(PNP)

TO-92 Bipolar Transistors

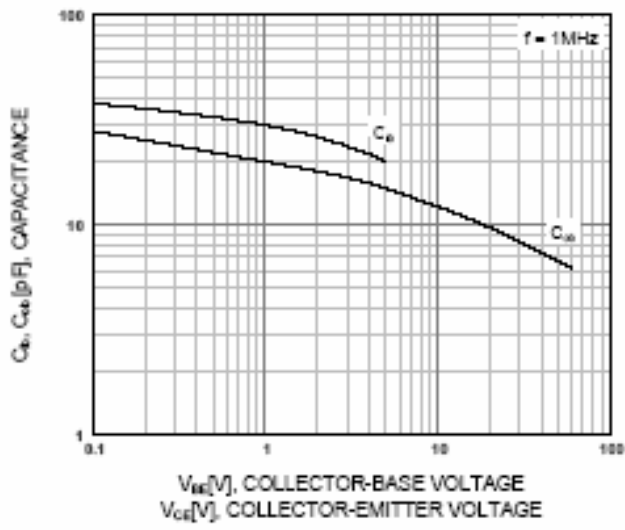


Figure 7. Input and Output Capacitance vs. Reverse Voltage

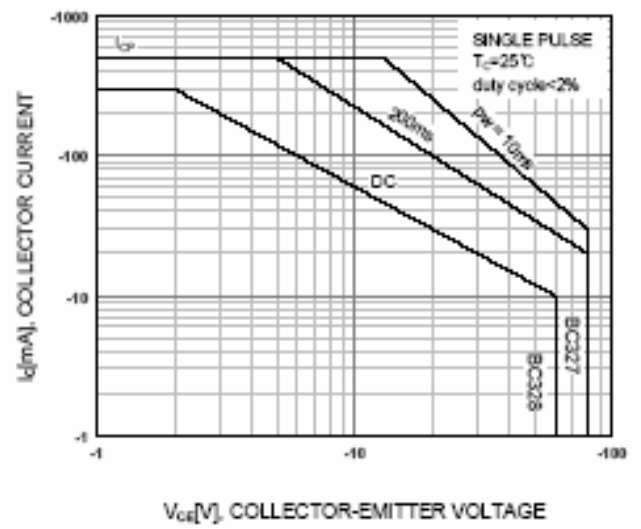


Figure 8. Safe Operating Area